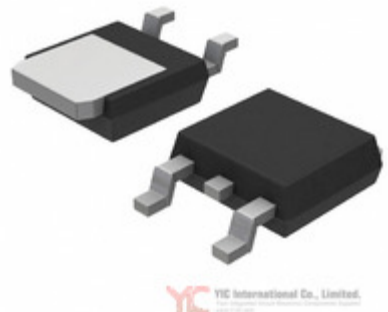

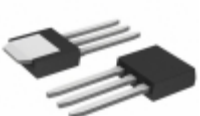
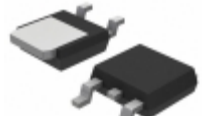





	<h2 style="color: red;">NTD12N10T4G</h2>	
	<b>Hersteller-Teilenummer:</b>	<a href="#">NTD12N10T4G</a>
	<b>Hersteller / Marke:</b>	<a href="#">AMI Semiconductor / ON Semiconductor</a>
	<b>Teil der Beschreibung:</b>	MOSFET N-CH 100V 12A DPAK
<b>Datenblätter:</b>	 <a href="#">NTD12N10T4G.pdf</a>	
<b>RoHs Status:</b>	Bleifrei / RoHS-konform	
<b>Lagerzustand:</b>	New original, 72441 pcs Stock Available.	
<b>Liefern von:</b>	Hong Kong	
<b>Versandweg:</b>	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

### Spezifikationen

Teilenummer	<a href="#">NTD12N10T4G</a>
Hersteller	<a href="#">AMI Semiconductor / ON Semiconductor</a>
Beschreibung	MOSFET N-CH 100V 12A DPAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	72441 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	DPAK
Verlustleistung (max)	1.28W (Ta), 56.6W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	12A (Ta)
Rds On (Max) @ Id, Vgs	165 mOhm @ 6A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	20nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	550pF @ 25V
Verpackung	Tape & Reel (TR)

NTD12N10T4G ist neu im Original, Suche NTD12N10T4G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NTD12N10T4G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NTD12N10T4G: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>NTD12N10-001</b> VB NTD12N10-001 VB</p>	 <p><b>NTD12N10-1G</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12A IPAK</p>	 <p><b>NTD14N03R</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 25V 2.5A DPAK</p>	 <p><b>NTD14N03R-1</b> O NTD14N03R-1 O</p>
 <p><b>NTD14N03R-001</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 25V 2.5A IPAK</p>	 <p><b>NTD14N03</b> ON NTD14N03 ON</p>	 <p><b>NTD12N10T4</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12A DPAK</p>	 <p><b>NTD12N10G</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12A DPAK</p>

### heiße Teile

Mehr

NTD110N02	NTD110N02R	NTD110N02R-001	NTD110N02R-001G	NTD110N02RG
NTD110N02RT4G	NTD12N10-001	NTD12N10-1G	NTD12N10G	NTD12N10T4
NTD14N03	NTD14N03G	NTD14N03R	NTD14N03R-001	NTD14N03R-1
NTD14N03R-1G	NTD14N03RG	NTD14N03RT4	NTD14N03RT4G	NTD14N03RTCG
NTD14N03T4G	NTD15N06	NTD15N06L	NTD15N06LG	NTD15N06LT4
NTD15N06LT4G	NTD15N06T4	NTD15N06T4G	NTD15N06VLT4	NTD15N07
NTD15N10	NTD18N06-001	NTD18N06-1G	NTD18N06G	NTD18N06L
NTD18N06L-1G	NTD18N06LG	NTD18N06LT4G	NTD18N06T4G	NTD20N03
NTD20N03G	NTD20N03HL	NTD20N03L27	NTD20N03L27G	NTD20N03L27T
NTD20N03L27T4	NTD20N03L27T4G	NTD20N03RT4G	NTD20N06	NTD20N06-001

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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